

REMARKS

Claims 1, 3, and 5-12 are pending in this application, the independent claims being claims 1 and 3. By this Amendment, claims 1 and 3 are amended to incorporate the subject matter of claim 2. Claim 2 is canceled. No new matter is added.

Reconsideration of the application is respectfully requested.

I. The Rejections Under 35 U.S.C. §112 Should Be Withdrawn

The Office Action rejects claims 1, 3, and 5-12 under 35 U. S. C. §112, second paragraph. Applicants respectfully traverse this rejection.

The subject matter of forming an island pattern by sputtering is described in the specification at, for example, Fig. 1b and page 9, lines 3-15. As disclosed, forming initial crystal nuclei of an electrode material in an island pattern by sputtering means forming an initial crystal nuclei of an electrode material by sputtering so that each of the initial crystal nuclei can be placed separately. Thus, the subject matter of forming an island pattern by sputtering is adequately disclosed and supported in the specification.

Accordingly, Applicants respectfully request withdrawal of the rejection under 35 U. S. C. §112, second paragraph.

II. The Rejections Under 35 U.S.C. 103(a) Should Be Withdrawn

The Office Action rejects claims 1, 3, 5-7 and 10-12 under 35 U. S. C. 103(a) over Summerfelt (U. S. Pat. No. 6,117,689) in view of Wolf (Silicon Processing for the VLSI Era, Vol 1: Process Technology, p. 335 and 375); rejects claim 2 under 35 U.S.C. §103(a) over Summerfelt and Wolf further in view of Norga (U. S. Pat. No. 6,545,856); and rejects claims 8 and 9 under 35 U.S.C. §103(a) over Summerfelt and Wolf and further in view of Basceri (U. S. Pat. No. 6,534,357). Applicants respectfully traverse these rejections.

Claim 1 is amended to incorporate the subject matter recited in claim 2, as outlined above. Claim 3 is similarly amended. Neither Summerfelt, Wolf, Norga, nor Basceri

discloses or suggests, either individually or in combination, a method of manufacturing an electrode over a substrate including the step of causing the initial crystal nuclei to be grown at a temperature lower than 200 °C by using an evaporation method, as originally recited in claim 2, and concurrently recited in claim 1 and similarly recited in claim 3.

The Office Action recognizes that Summerfelt does not disclose or suggest the subject matter recited in claim 2, but asserts that Norga supplies this missing subject matter.

However, Norga does not supply the subject matter lacking in Summerfelt.

Norga teaches sputtering at substrate temperature between 150 and 350 °C. See col. 9, lines 55-67. However, the cited temperature is unrelated to an evaporation method. Norga does not disclose forming nuclei using an evaporation method. Thus, Norga does not disclose growing nuclei at a temperature lower than a temperature lower than 200 °C by using an evaporation method. Therefore, Norga fails to supply the subject matter that is lacking in Summerfelt.

Wolf and Basceri do not supply the subject matter lacking in Summerfelt. Therefore, Summerfelt, Wolf, Norga and Basceri, either individually or in combination, do not disclose or suggest the subject matter recited in claims 1 and 3, and claims 5-12 depending therefrom.

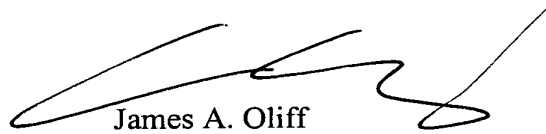
Accordingly, Applicants respectfully request that the rejection under 35 U.S.C. §103(a) be withdrawn.

III. Conclusion

In view of the foregoing amendments and remarks, Applicants submit that this application is in condition for allowance. Favorable consideration and prompt allowance of claims 1, 3, and 5-12 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



James A. Oliff
Registration No. 27,075

Gang Luo
Registration No. 50,559

JAO:GXL/mef

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OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

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